

FIG. 1

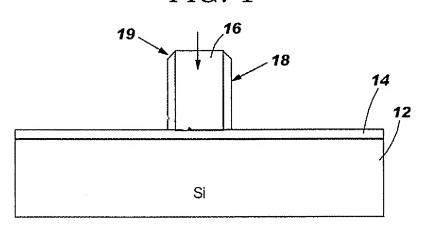


FIG. 2

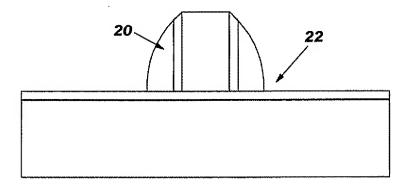
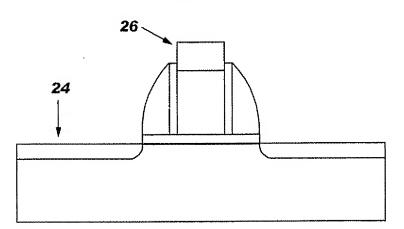
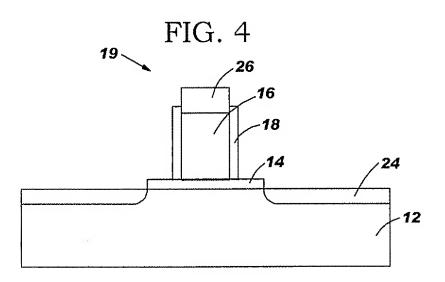


FIG. 3





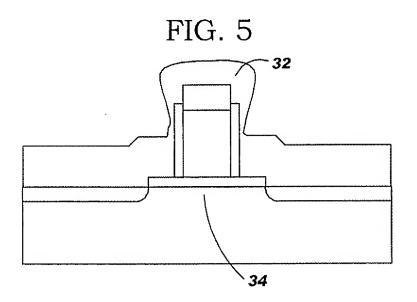
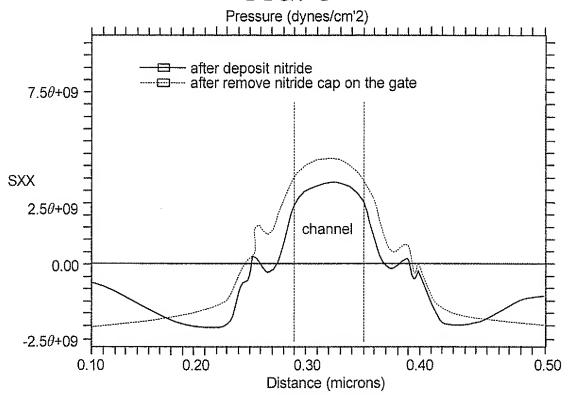


FIG. 6



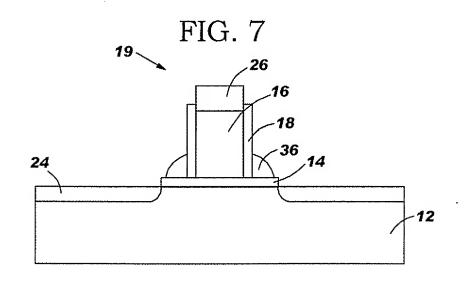




FIG. 8

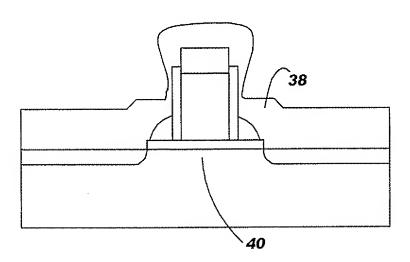
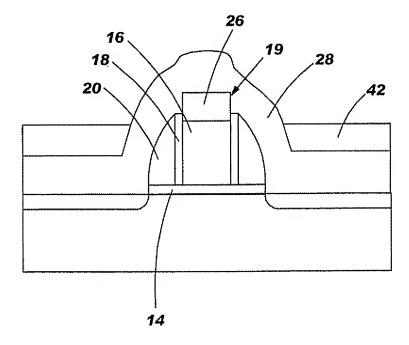


FIG. 9



Application No. 10/707,842 Confirmation No. 1841
Applicant: Haining S. YANG, et. al. Attorney Docket No. P27165
Title: METHOD AND APPARATUS FOR INCREASE STRAIN EFFECT
IN A TRANSISTOR CHANNEL

Responsive to Official Communication dated: December 27, 2005
REPLACEMENT SHEET

6/7 FIG. 10

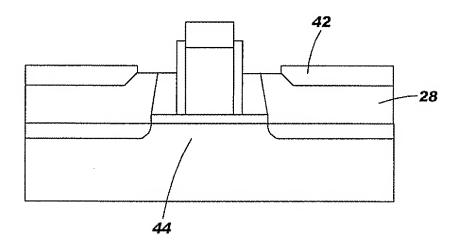


FIG. 11

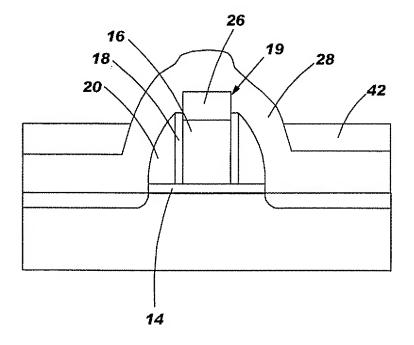


FIG. 12

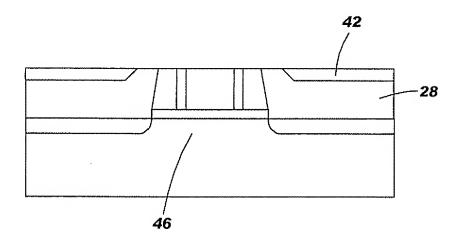


FIG. 13

